

The substitution of claims 1-8 has been done to merely place this national phase application in into the same condition as it was during Chapter II of the International Phase.

Entry of the above amendments is earnestly solicited. An early and favorable first action on the merits is earnestly requested.

Should there be any matters that need to be resolved in the present application, the Examiner is respectfully requested to contact the undersigned at the telephone number listed below.

Attached hereto is a marked-up version of the changes made to the claims by the current amendment. The attached page is captioned "VERSION WITH MARKINGS TO SHOW CHANGES MADE."

The Commissioner is hereby authorized in this, concurrent, and future replies, to charge payment or credit any overpayment to Deposit Account No. 25-0120 for any additional fees required under 37 C.F.R. § 1.16 or under 37 C.F.R. § 1.17.

Respectfully submitted,

YOUNG & THOMPSON



Benoit Castel, Reg. No. 35,041

745 South 23rd Street
Arlington, VA 22202
Telephone (703) 521-2297

BC/lmt
Attachments

VERSION WITH MARKINGS TO SHOW CHANGES MADE

IN THE CLAIMS:

The claims have been amended as follows:

--3. (amended) Method according to Claim ~~1 or 2~~ characterized in that the doping material (2) is first applied to the substrate, after which the barrier material (5, 5', 5'') is applied to the substrate on the doping material (2).--

--4. (amended) Method according to ~~one of the preceding claims,~~ claim 1, characterized in that the diffusion barrier material (5, 5', 5'') is a dielectric material in paste form that is sintered after being applied to the substrate (1).--

--6. (amended) Method according to ~~one of the preceding claims,~~ claim 1, characterized in that the surface resistance of the highly doped regions is between 10 and 60 ohm square and the surface resistance of the regions of low doping is between 30 and 500 ohm square.--

--8. (amended) Method according to ~~one of the preceding claims,~~ claim 1, characterized in that an etching material is added to the diffusion material (5, 5', 5'') to etch away the substrate.--